

40V NPN SMALL SIGNAL TRANSISTOR IN SOT323

Features

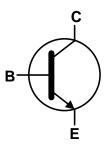
- BV_{CEO} > 40V
- I_C = 200mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMST3906
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

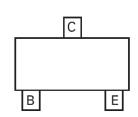
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.006 grams (Approximate)







Device Symbol



Pin-out Top View

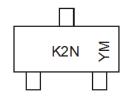
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMST3904-7-F	Standard	K2N	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K2N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2018	8	2019	2020	2021	2022	2023	2024	4 20	25 2	2026	2027	2028
Code	F		G	Н		J	K	L	N	Л	N	0	Р
Month	1	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	!	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	Ic	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

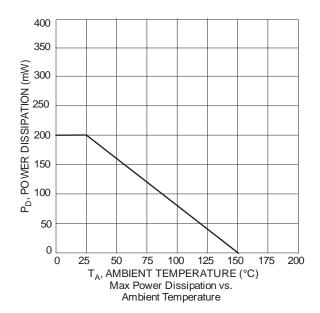
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





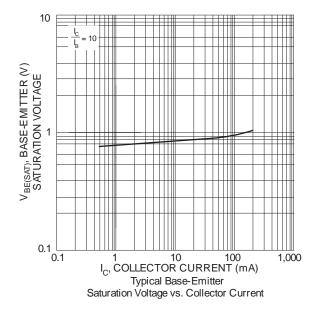
Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

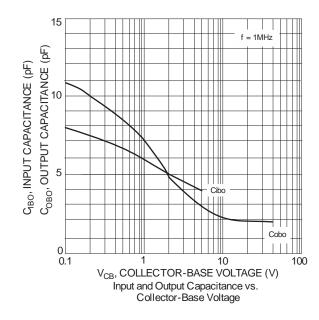
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	_	V	$I_C = 1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}		50	nA	$V_{CE} = 30V$, $V_{EB(OFF)} = 3V$
Base Cutoff Current	I_{BL}	_	50	nA	$V_{CE} = 30V$, $V_{EB(OFF)} = 3V$
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	40 70 100 60 30	300 — —	_	$I_{C} = 100\mu A, V_{CE} = 1V$ $I_{C} = 1mA, V_{CE} = 1V$ $I_{C} = 10mA, V_{CE} = 1V$ $I_{C} = 50mA, V_{CE} = 1V$ $I_{C} = 100mA, V_{CE} = 1V$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.25 0.30	V	$I_C = 10mA$, $I_B = 1mA$ $I_C = 50mA$, $I_B = 5mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	$I_C = 10mA, I_B = 1mA$ $I_C = 50mA, I_B = 5mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	_	4	pF	$V_{CB} = 5V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_{ibo}	_	8	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{ie}	1	10	kΩ	
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0MHz
Output Admittance	h _{oe}	1	40	μS	
Current Gain-Bandwidth Product	f _T	300		MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF		5	dB	$V_{CC} = 5V, I_C = 100\mu A,$ $R_S = 1k\Omega, f = 1MHz$
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	$V_{CC} = 3V$, $I_C = 10mA$,
Rise Time	tr	1	35	ns	$V_{BE(OFF)} = -0.5V$, $I_{B1} = 1mA$
Storage Time	ts		200	ns	$V_{CC} = 3.0V, I_C = 10mA,$
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

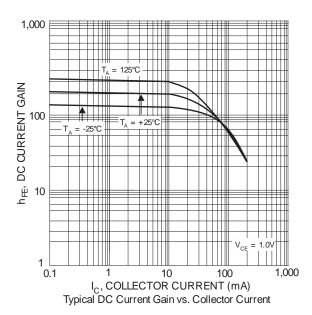
Note: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

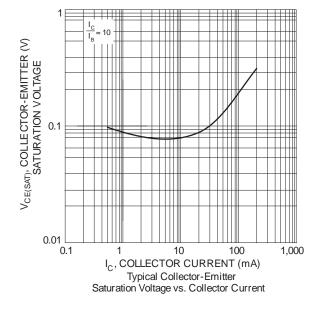


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







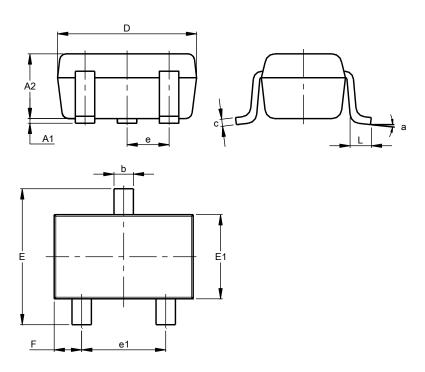




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

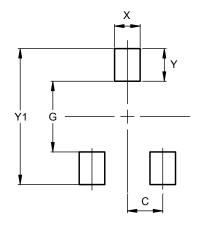


		T000					
SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value
Dillielisions	(in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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